

RBV600D - RBV610D

SILICON BRIDGE RECTIFIERS

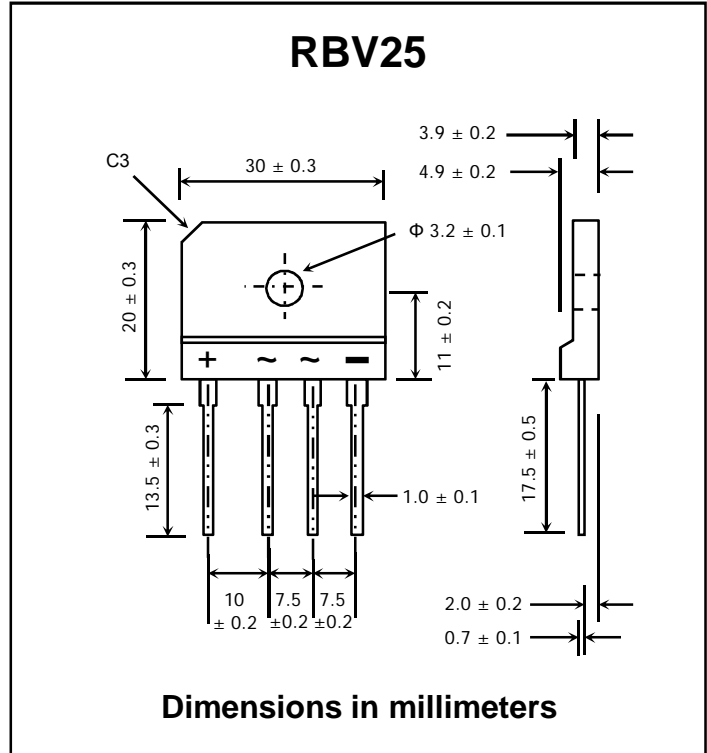
PRV : 50 - 1000 Volts
Io : 6.0 Amperes

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Rated isolation-voltage 2000 V_{AC}
- * Ideal for printed circuit board
- * Very good heat dissipation
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-0 rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 7.80 grams (Approximaly)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	RBV 600D	RBV 601D	RBV 602D	RBV 604D	RBV 606D	RBV 608D	RBV 610D	UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current T _c = 55°C	I _{F(AV)}	6.0							A
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I _{FSM}	300							A
Current Squared Time at t < 8.3 ms.	I ² t	373							A ² s
Maximum Forward Voltage per Diode at I _F = 6.0 A	V _F	1.0							V
Maximum DC Reverse Current Ta = 25 °C at Rated DC Blocking Voltage Ta = 100 °C	I _R	10							μA
	I _{R(H)}	200							μA
Typical Thermal Resistance (Note 1)	R _{θJC}	2.2							°C/W
Operating Junction Temperature Range	T _J	- 40 to + 150							°C
Storage Temperature Range	T _{STG}	- 40 to + 150							°C

Note : 1. Thermal Resistance from junction to case with units mounted on a 2.6"x1.4"x0.06" THK (6.5cm.x3.5cm.x0.15cm.) Al. Plate. Heatsink.

RATING AND CHARACTERISTIC CURVES (RBV600D - RBV610D)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

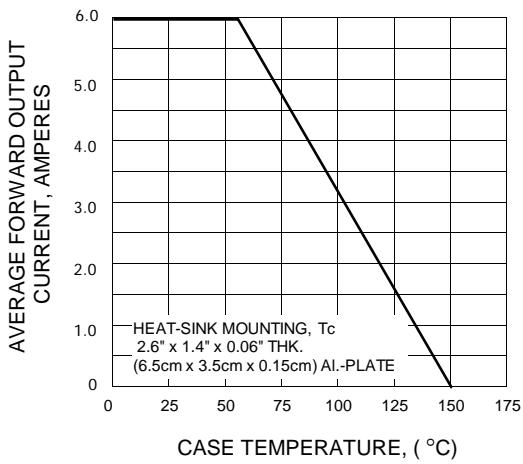


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

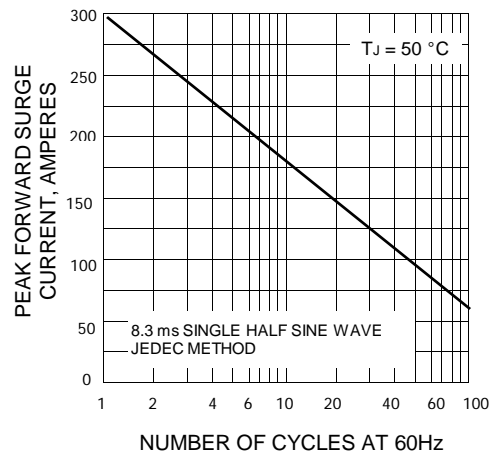


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

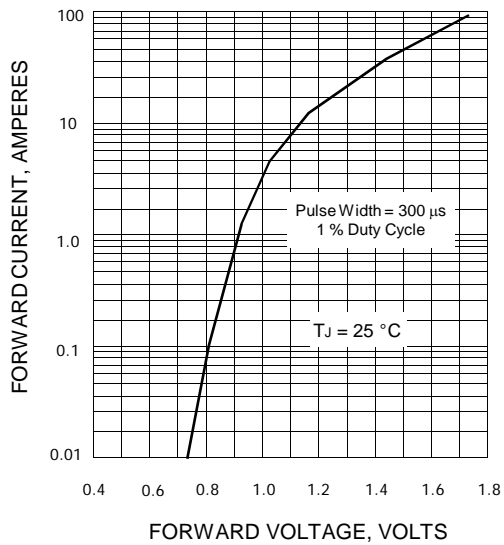


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

